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Comment on "Electric Field Scaling at $B = 0$ Metal-Insulator Transition in Two Dimensions"

In a recent Letter, Kravchenko et al. [1] have provided evidence for a metal-insulator transition (MIT) in a two-dimensional electron system (2DES) in Si metal-oxide-semiconductor field-effect transistors (MOSFETs). The transition observed in these samples [1,2] occurs at relatively low electron densities $n_s \sim (1-2)\times 10^{11}\mathrm{cm}^{-2}$ so that the electron-electron interaction $U \propto \sqrt{n_s}$ is about an order of magnitude greater than the Fermi energy $E_F \propto n_s$, suggesting that this MIT is driven by electron-electron interactions. However, the disorder in Si MOSFETs at the transition is also strong, as indicated by the reported [1,2] values of the critical conductivity $\sigma_c \sim e^2/2h$.

In this Comment, we present evidence for a 2D MIT in another Si-based structure where the disorder, as measured by the mobility, is about two orders of magnitude weaker than in Si MOSFETs. We find that the MIT occurs in the same range of n_s as in Si MOSFETs. This provides clear and strong evidence that the 2D MIT in Si-based devices is caused by electron-electron interactions.

The measurements were carried out on a 2DES located in a 10 nm thick Si channel sandwiched between a $\mathrm{Si}_{0.75}\mathrm{Ge}_{0.25}$ buffer ($\sim$ 1.5 μm thick) and a 15 nm thick $\mathrm{Si}_{0.75}\mathrm{Ge}_{0.25}$ spacer, which was followed by a 10 nm thick $\mathrm{Si}_{0.75}\mathrm{Ge}_{0.25}$ supply layer ($N_D = 4\times 10^{18}\mathrm{cm}^{-3}$), and a 4 nm thick Si cap layer ($N_D = 4-10\times 10^{18}\mathrm{cm}^{-3}$) [3]. The samples were standard Hall bars with a source-to-drain length $L = 100$ μm and a width $W = 10$ μm. Resistance R was measured using ac lock-in techniques at temperatures $0.35 < T < 4.2$ K as a function of the carrier density n_s, which was varied using the front gate at a fixed back-gate bias V_{BG}. The effect of the V_{BG} was to change the mobility of a 2DES at a given n_s.

Fig. 1(a) shows the conductivity $\sigma = L/(WR)$ as a function of n_s at several T. Clearly, for $n_s > n_c \approx 1.8\times 10^{11}\mathrm{cm}^{-2}$, σ exhibits the metallic T-dependence: it increases as T is lowered. For $n_s < n_c$, the T-dependence is reversed, i. e. it is insulating. Scaling of σ with T [1,2] is shown in Fig. 1(b) with the scaling exponent of 4±1 but more work is in progress in order to determine its value more precisely. Even though these data look very similar to the results obtained on Si MOSFETs [1,2], there is at least one striking difference: $\sigma_c \sim 100$ e^2/h. Therefore, it is clear that the value of σ_c at a 2D MIT is *not* universal. Very high mobilities have been reported earlier [3] in these modulation-doped Si/SiGe heterostructures. For example, the mobility $\mu = \sigma/n_s e$ at the MIT in Fig. 1(a) is of the order of 100,000 cm^2/Vs, whereas μ ∼1,000 cm^2/Vs at the MIT in Si MOSFETs [1,2]. Our most important result, however, is that the MIT in Si/SiGe heterostructures occurs for n_c comparable to those in Si MOSFETs, so that U at the MIT in both types of samples is about the same. On the other hand, our Si/SiGe samples are very weakly disordered: $k_F l \approx 40$ (k_F – Fermi wavenumber, l – mean free path) at $n_s = n_c$ in these samples, as opposed to $k_F l \lesssim 1$ in Si MOSFETs. These results provide clear and convincing evidence that U is the relevant energy scale at the MIT in Si-based devices, and not disorder. Since Si is a multivalley semiconductor, it would be interesting to study this transition in other multivalley and single valley semiconductors.

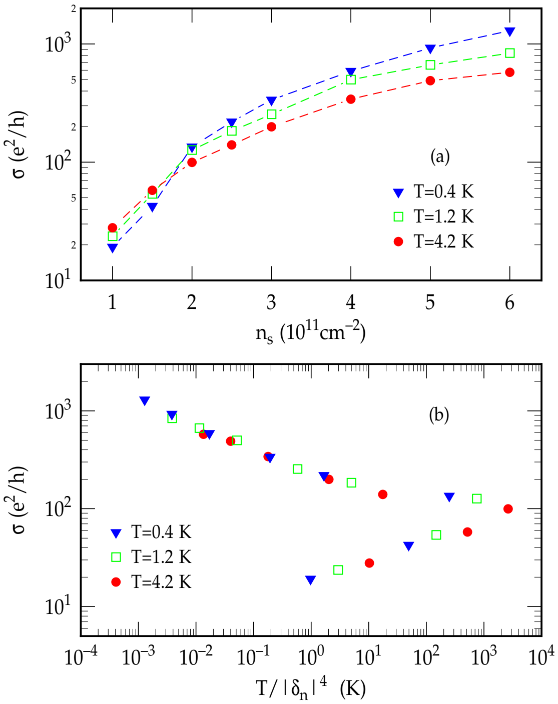

FIG. 1. (a) σ vs. n_s for $T = 4.2, 1.2, 0.4$ K and $V_{BG} = 10$ V. The critical density $n_c \approx 1.8\times 10^{11}\mathrm{cm}^{-2}$. (b) Scaling of σ with T using the data shown in (a). $\delta_n \equiv (n_s - n_c)/n_c$.

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